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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	56800EX
Core Size	32-Bit Single-Core
Speed	60MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	54
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 16x12b, 8x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc56f84452vlh

- 
- Operating characteristics
 - Single supply: 3.0 V to 3.6 V
 - 5 V–tolerant I/O
 - LQFP packages:
 - 48-pin
 - 64-pin

- Up to 16 KW FlexNVM, which can be used as additional program or data flash memory
- Up to 1 KW FlexRAM, which can be configured as enhanced EEPROM (used in conjunction with FlexNVM) or used as additional RAM

1.5 Interrupt Controller

- Five interrupt priority levels
 - Three user programmable priority levels for each interrupt source: level 0, 1, 2
 - Unmaskable level 3 interrupts include: illegal instruction, hardware stack overflow, misaligned data access, SWI3 instruction
 - Maskable level 3 interrupts include: EOnCE step counter, EOnCE breakpoint unit, EOnCE trace buffer
 - Lowest-priority software interrupt: level LP
- Support for nested interrupt: higher priority level interrupt request can interrupt lower priority interrupt subroutine
- Masking of interrupt priority level managed by the 56800EX core
- Two programmable fast interrupts that can be assigned to any interrupt source
- Notification to System Integration Module (SIM) to restart clock when in wait and stop states
- Ability to relocate interrupt vector table

1.6 Peripheral highlights

1.6.1 Enhanced Flex Pulse Width Modulator (eFlexPWM)

- Up to 12 output channels in each module
- 16 bits of resolution for center, edge aligned, and asymmetrical PWMs
- PWMA with accumulative fractional clock calculation
 - Accumulative fractional clock calculation improves the resolution of the PWM period and edge placement
 - Arbitrary PWM edge placement
 - Equivalent to 312 ps PWM frequency and duty-cycle resolution on average
- Each complementary pair can operate with its own PWM frequency base and deadtime values
 - 4 time base in each PWM module
 - Independent top and bottom deadtime insertion for each complementary pair
- PWM outputs can operate as complementary pairs or independent channels
- Independent control of both edges of each PWM output

- Enhanced input capture and output compare functionality on each input
 - Channels not used for PWM generation can be used for buffered output compare functions
 - Channels not used for PWM generation can be used for input capture functions
 - Enhanced dual edge capture functionality
- Synchronization to external hardware or other PWM supported
- Double buffered PWM registers
 - Integral reload rates from 1 to 16
 - Half-cycle reload capability
- Multiple output trigger events can be generated per PWM cycle via hardware
- Support for double switching PWM outputs
- Up to eight fault inputs can be assigned to control multiple PWM outputs
 - Programmable filters for fault inputs
- Independently programmable PWM output polarity
- Individual software control of each PWM output
- All outputs can be programmed to change simultaneously via a FORCE_OUT event
- PWMX pin can optionally output a third PWM signal from each submodule
- Option to supply the source for each complementary PWM signal pair from any of the following:
 - Crossbar module outputs
 - External ADC input, taking into account values set in ADC high and low limit registers

1.6.2 12-bit Analog-to-Digital Converter (Cyclic type)

- Two independent 12-bit analog-to-digital converters (ADCs)
 - 2 x 8-channel external inputs
 - Built-in x1, x2, x4 programmable gain pre-amplifier
 - Maximum ADC clock frequency is up to 20 MHz with 50 ns period
 - Single conversion time of 8.5 ADC clock cycles
 - Additional conversion time of 6 ADC clock cycles
- Sequential, parallel, and independent scan mode
- First 8 samples have offset, limit and zero-crossing calculation supported
- ADC conversions can be synchronized by any module connected to internal crossbar module, such as PWM and timer modules and GPIO and comparators
- Support for simultaneous and software triggering conversions
- Support for multi-triggering mode with a programmable number of conversions on each trigger
- Each ADC has ability to scan and store up to 8 conversion results

1.6.7 Queued Serial Communications Interface (QSCI) Modules

- Operating clock up to two times CPU operating frequency
- Four-word-deep FIFOs available on both transmit and receive buffers
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit integer and 3-bit fractional baud rate selection
- Full-duplex or single-wire operation
- Programmable 8-bit or 9-bit data format
- Error detection capability
- Two receiver wakeup methods:
 - Idle line
 - Address mark
- 1/16 bit-time noise detection

1.6.8 Queued Serial Peripheral Interface (QSPI) Modules

- Maximum 25 Mbps baud rate
- Selectable baud rate clock sources for low baud rate communication
- Baud rate as low as $\text{Baudrate_Freq_in} / 8192$
- Full-duplex operation
- Master and slave modes
- Double-buffered operation with separate transmit and receive registers
- Four-word-deep FIFOs available on transmit and receive buffers
- Programmable length transmissions (2 bits to 16 bits)
- Programmable transmit and receive shift order (MSB as first bit transmitted)

1.6.9 Inter-Integrated Circuit (I2C)/System Management Bus (SMBus) Modules

- Compatible with I2C bus standard
- Support for System Management Bus (SMBus) specification, version2
- Multi-master operation
- General call recognition
- 10-bit address extension
- Dual slave addresses
- Programmable glitch input filter

1.6.10 Flex Controller Area Network (FlexCAN) Module

- Clock source from PLL or XOSC/CLKIN

- Implementation of the CAN protocol Version 2.0 A/B
- Standard and extended data frames
- 0-to-8 bytes data length
- Programmable bit rate up to 1 Mbps
- Support for remote frames
- Sixteen Message Buffers, each configurable as receive or transmit, all supporting standard and extended messages
- Individual Rx Mask Registers per Message Buffer
- Internal timer for time-stamping of received and transmitted messages
- Listen-only mode capability
- Programmable loopback mode supporting self-test operation
- Programmable transmission priority scheme: lowest ID, lowest buffer number, or highest priority
- Global network time, synchronized by a specific message
- Low power modes, with programmable wakeup on bus activity

1.6.11 Computer Operating Properly (COP) Watchdog

- Programmable timeout period
- Support for operation in all power modes: run mode, wait mode, stop mode
- Causes loss of reference reset 128 cycles after loss of reference clock to the PLL is detected
- Selectable reference clock source in support of EN60730 and IEC61508
- Selectable clock sources:
 - External crystal oscillator/external clock source
 - On-chip low-power 32 kHz oscillator
 - System bus (IPBus up to 60 MHz)
 - 8 MHz / 400 kHz ROSC
- Support for interrupt triggered when the counter reaches the timeout value

1.6.12 Power Supervisor

- Power-on reset (POR) to reset CPU, peripherals, and JTAG/EOnCE controllers ($VDD > 2.1\text{ V}$)
- Brownout reset ($VDD < 1.9\text{ V}$)
- Critical warn low voltage interrupt (LVI2.0)
- Peripheral low voltage interrupt (LVI2.7)

1.6.13 Phase Locked Loop

- Wide programmable output frequency: 240 MHz to 400 MHz
- Input reference clock frequency: 8 MHz to 16 MHz
- Detection of loss of lock and loss of reference clock
- Ability to power down

1.6.14 Clock sources

1.6.14.1 On-Chip Oscillators

- Tunable 8 MHz relaxation oscillator with 400 kHz at standby mode (divide-by-two output)
- 32 kHz low frequency clock as secondary clock source for COP, EWM, PIT

1.6.14.2 Crystal Oscillator

- Support for both high ESR crystal oscillator (greater than 100-ohm ESR) and ceramic resonator
- 4 MHz to 16 MHz operating frequency

1.6.15 Cyclic Redundancy Check (CRC) Generator

- Hardware 16/32-bit CRC generator
- High-speed hardware CRC calculation
- Programmable initial seed value
- Programmable 16/32-bit polynomial
- Error detection for all single, double, odd, and most multi-bit errors
- Option to transpose input data or output data (CRC result) bitwise or byte-wise,¹ which is required for certain CRC standards
- Option for inversion of final CRC result

1.6.16 General Purpose I/O (GPIO)

- 5 V tolerance
- Individual control of peripheral mode or GPIO mode for each pin
- Programmable push-pull or open drain output
- Configurable pullup or pulldown on all input pins

1. A byte-wise transposition is not possible when accessing the CRC data register via 8-bit accesses. In this case, user software must perform the byte-wise transposition.

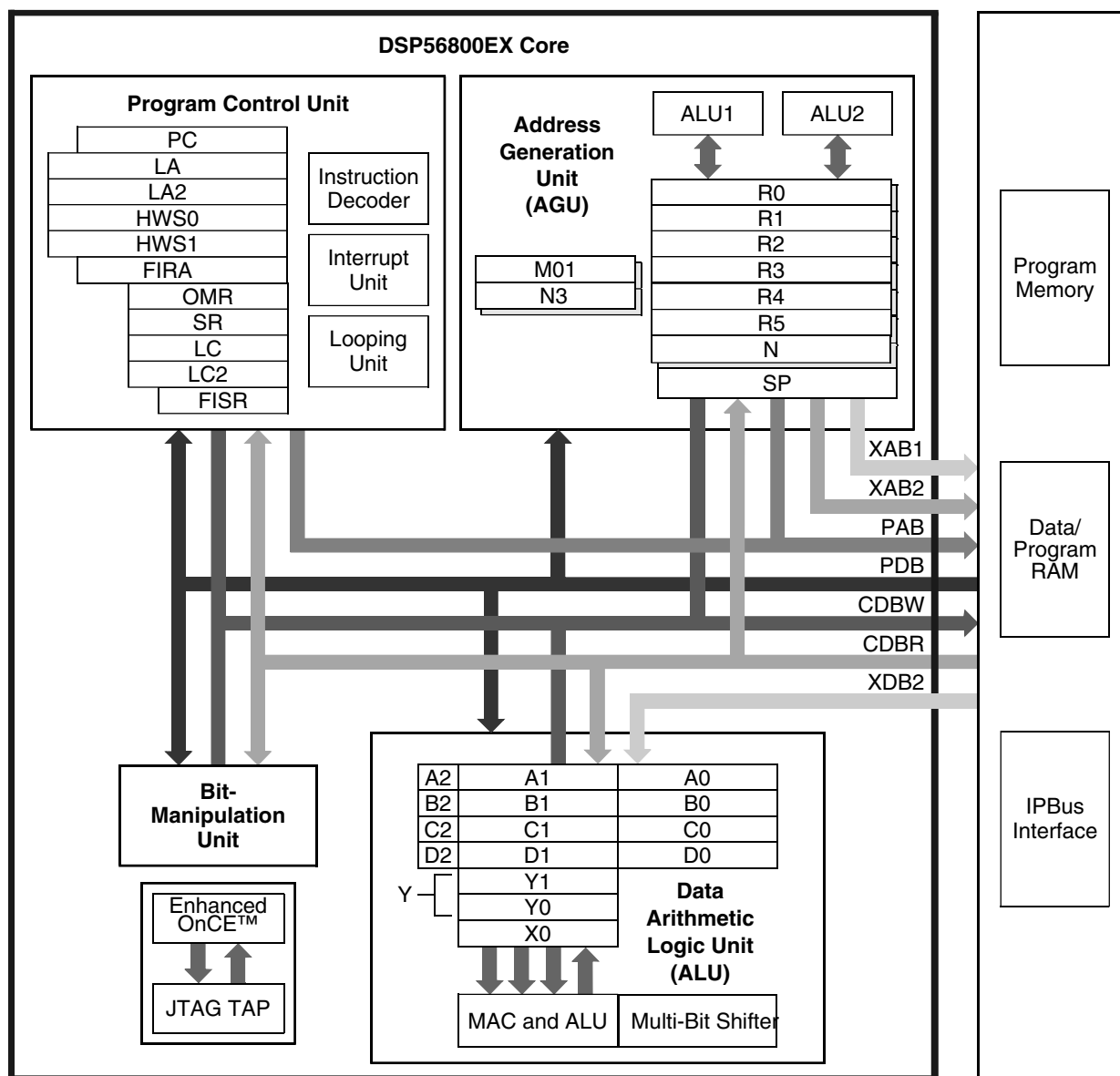


Figure 1. 56800EX Basic Block Diagram

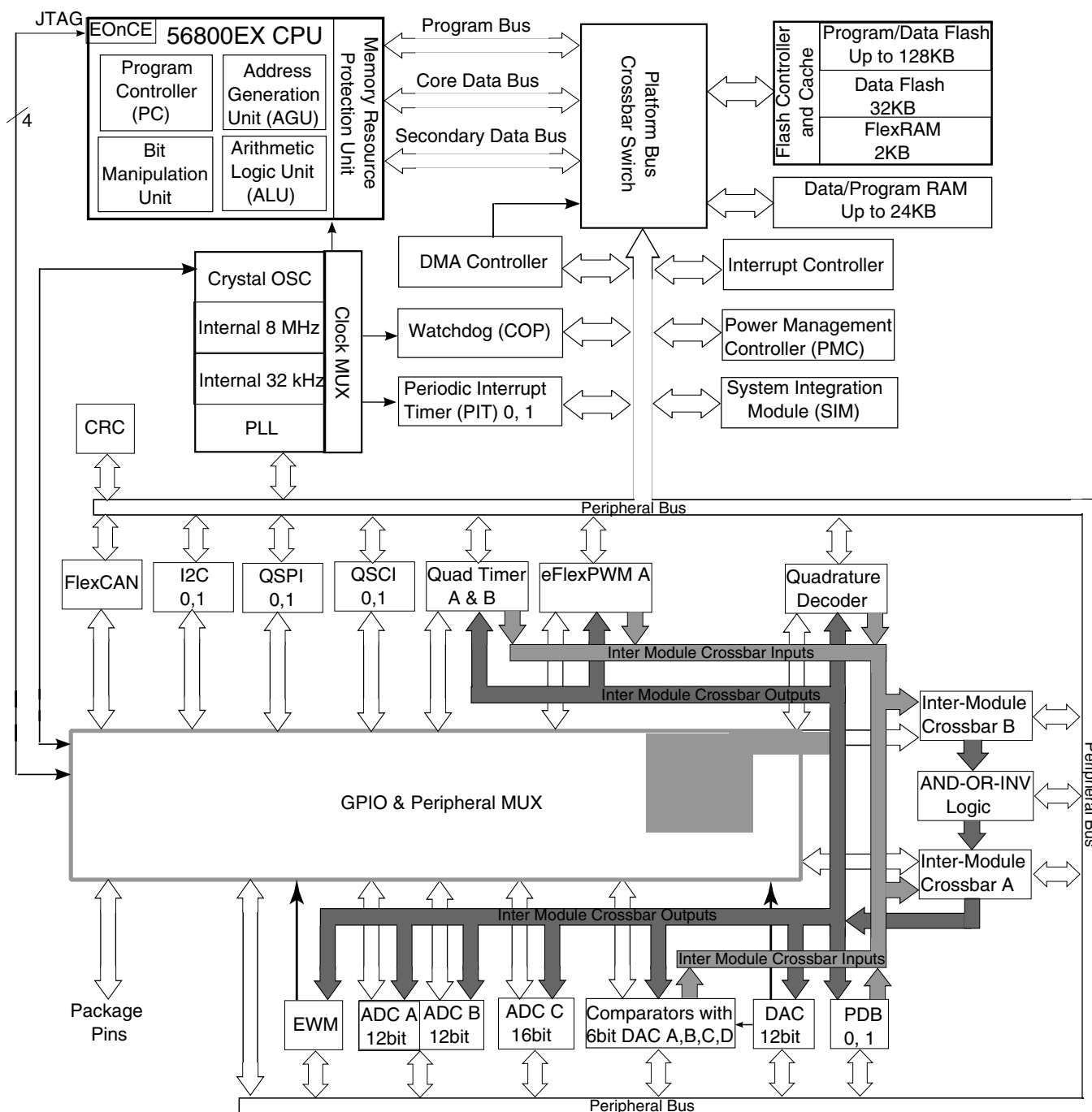


Figure 2. System Diagram

5.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

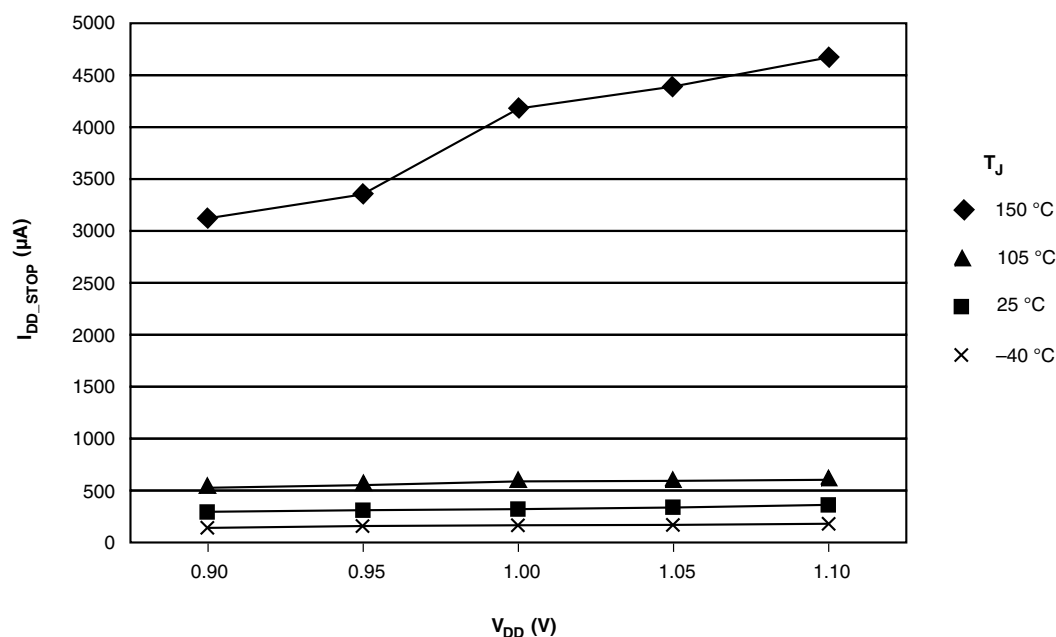
5.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

5.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



Absolute maximum ratings in [Table 4](#) are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond these ratings may affect device reliability or cause permanent damage to the device.

Unless otherwise stated, all specifications within this chapter apply over the temperature range of -40°C to 105°C ambient temperature over the following supply ranges:

$V_{SS} = V_{SSA} = 0\text{ V}$, $V_{DD} = V_{DDA} = 3.0\text{ V}$ to 3.6 V , $CL \leq 50\text{ pF}$, $f_{OP} = 60\text{ MHz}$.

CAUTION

This device contains protective circuitry to guard against damage due to high static voltage or electrical fields. However, normal precautions are advised to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate voltage level.

7.2 AC Electrical Characteristics

Tests are conducted using the input levels specified in [Table 7](#). Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured between the 10% and 90% points, as shown in [Figure 3](#).

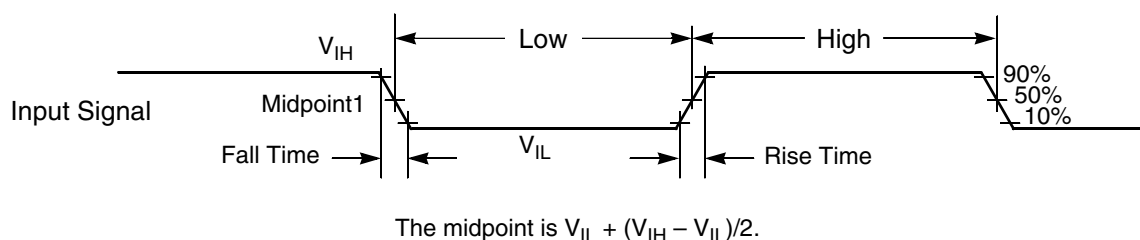


Figure 3. Input Signal Measurement References

[Figure 4](#) shows the definitions of the following signal states:

- Active state, when a bus or signal is driven, and enters a low impedance state
- Tri-stated, when a bus or signal is placed in a high impedance state
- Data Valid state, when a signal level has reached V_{OL} or V_{OH}
- Data Invalid state, when a signal level is in transition between V_{OL} and V_{OH}

7.3.5 Power consumption operating behaviors

Table 9. Current Consumption

Mode	Maximum Frequency	Conditions	Typical at 3.3 V, 25°C		Maximum at 3.6 V, 105°C	
			I _{DD} ¹	I _{DDA}	I _{DD} ¹	I _{DDA}
RUN	60 MHz	<ul style="list-style-type: none"> 60 MHz Device Clock Regulators are in full regulation Relaxation Oscillator on PLL powered on Continuous MAC instructions with fetches from Program Flash All peripheral modules enabled. TMRs and SCIs using 1X Clock NanoEdge within PWMA using 2X clock ADC/DAC powered on and clocked at 5 MHz² Comparator powered on 	TBD	TBD	TBD	TBD
WAIT	60 MHz	<ul style="list-style-type: none"> 60 MHz Device Clock Regulators are in full regulation Relaxation Oscillator on PLL powered on Processor Core in WAIT state All Peripheral modules enabled. TMRs and SCIs using 1X Clock NanoEdge within PWMA using 2X clock ADC/DAC/Comparator powered off 	TBD	TBD	TBD	TBD
STOP	4 MHz	<ul style="list-style-type: none"> 4 MHz Device Clock Regulators are in full regulation Relaxation Oscillator on PLL powered off Processor Core in STOP state All peripheral module and core clocks are off ADC/DAC/Comparator powered off 	TBD	TBD	TBD	TBD
LPRUN (LsRUN)	2 MHz	<ul style="list-style-type: none"> 200 kHz Device Clock from Relaxation Oscillator (ROSC) ROSC in standby mode Regulators are in standby PLL disabled Repeat NOP instructions All peripheral modules enabled, except NanoEdge and cyclic ADCs³ Simple loop with running from platform instruction buffer 	TBD	TBD	TBD	TBD
LPWAIT (LsWAIT)	2 MHz	<ul style="list-style-type: none"> 200 kHz Device Clock from Relaxation Oscillator (ROSC) ROSC in standby mode Regulators are in standby PLL disabled All peripheral modules enabled, except NanoEdge and cyclic ADCs³ Processor core in wait mode 	TBD	TBD	TBD	TBD

Table continues on the next page...

8.3.3 External Crystal or Resonator Requirement

Table 20. Crystal or Resonator Requirement

Characteristic	Symbol	Min	Typ	Max	Unit
Frequency of operation	f_{XOSC}	4	8	16	MHz

8.3.4 Relaxation Oscillator Timing

Table 21. Relaxation Oscillator Electrical Specifications

Characteristic	Symbol	Min	Typ	Max	Unit
8 MHz Output Frequency ¹					
RUN Mode					
• 0°C to 105°C		7.84	8	8.16	MHz
• -40°C to 105°C		7.76	8	8.24	
Standby Mode (IRC trimmed @ 8 MHz)					
• -40°C to 105°C		TBD	TBD	TBD	kHz
8 MHz Frequency Variation					
RUN Mode					
Due to temperature					
• 0°C to 105°C			+/-1.5	+/-2	%
• -40°C to 105°C			+/- 1.5	+/-3	
Standby Mode			Unspecified		
32 kHz Output Frequency ²					
RUN Mode					
• -40°C to 105°C		TBD	32	TBD	kHz
32 kHz Output Frequency Variation					
RUN Mode					
Due to temperature					
• -40°C to 105°C			+/-2.5	+/-4	%
Stabilization Time	tstab				
• 8 MHz output ³			0.12	0.4	μs
• 32 kHz output ⁴			14.4	16.2	
Output Duty Cycle		48	50	52	%

1. Frequency after application of 8 MHz trim
2. Frequency after application of 32 kHz trim
3. Standby to run mode transition
4. Power down to run mode transition

Table 23. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{ewr8b8k}	Byte-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
t_{ewr8b16k}	• 16 KB EEPROM backup	—	385	1800	μs	
t_{ewr8b32k}	• 32 KB EEPROM backup	—	475	2000	μs	
Word-write to FlexRAM for EEPROM operation						
$t_{\text{ewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
t_{ewr16b8k}	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{ewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{ewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{ewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
t_{ewr32b8k}	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{ewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{ewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

8.4.1.2 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nmretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
t_{nmretp1k}	Data retention after up to 1 K cycles	20	100	—	years	
η_{nmccyp}	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{\text{nmretd10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
t_{nmretd1k}	Data retention after up to 1 K cycles	20	100	—	years	
η_{nmccyd}	Cycling endurance	10 K	50 K	—	cycles	2
FlexRAM as EEPROM						
$t_{\text{nmreteee100}}$	Data retention up to 100% of write endurance	5	50	—	years	
$t_{\text{nmreteee10}}$	Data retention up to 10% of write endurance	20	100	—	years	

Table continues on the next page...

Table 24. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
	Write endurance					3
$n_{\text{nvmwree16}}$	• EEPROM backup to FlexRAM ratio = 16	35 K	175 K	—	writes	
$n_{\text{nvmwree128}}$	• EEPROM backup to FlexRAM ratio = 128	315 K	1.6 M	—	writes	
$n_{\text{nvmwree512}}$	• EEPROM backup to FlexRAM ratio = 512	1.27 M	6.4 M	—	writes	
$n_{\text{nvmwree4k}}$	• EEPROM backup to FlexRAM ratio = 4096	10 M	50 M	—	writes	
$n_{\text{nvmwree8k}}$	• EEPROM backup to FlexRAM ratio = 8192	20 M	100 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.
3. Write endurance represents the number of writes to each FlexRAM location at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$ influenced by the cycling endurance of the FlexNVM (same value as data flash) and the allocated EEPROM backup. Minimum and typical values assume all byte-writes to FlexRAM.

8.5 Analog

8.5.1 12-bit Cyclic Analog-to-Digital Converter (ADC) Parameters

Table 25. 12-bit ADC Electrical Specifications

Characteristic	Symbol	Min	Typ	Max	Unit
Recommended Operating Conditions					
Supply Voltage ¹	V_{DDA}	2.7	3.3	3.6	V
Vrefh Supply Voltage ²	V_{refhx}	3.0		V_{DDA}	V
ADC Conversion Clock ³	f_{ADCCLK}	0.6		20	MHz
Conversion Range	R_{AD}	V_{REFL}		V_{REFH}	V
Input Voltage Range ⁴	V_{ADIN}				V
External Reference		V_{REFL}		V_{REFH}	
Internal Reference		V_{SSA}		V_{DDA}	
Timing and Power					
Conversion Time	t_{ADC}		6		ADC Clock Cycles
Sample Time	t_{ADS}	1		5	ADC Clock Cycles
ADC Power-Up Time (from adc_pdn)	t_{ADPU}		13		ADC Clock Cycles

Table continues on the next page...

Table 25. 12-bit ADC Electrical Specifications (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ADC RUN Current (per ADC block) <ul style="list-style-type: none"> at 600 kHz ADC Clock, LP mode ≤ 8.33 MHz ADC Clock, 00 mode ≤ 12.5 MHz ADC Clock, 01 mode ≤ 16.67 MHz ADC Clock, 10 mode ≤ 20 MHz ADC Clock, 11 mode 	I_{ADRUN}		1 5 9 15 19		mA
ADC Powerdown Current (adc_pdn enabled)	$I_{ADPWRDWN}$		0.02		μA
V_{REFH} Current	I_{VREFH}		0.001		μA
Accuracy (DC or Absolute)					
Integral non-Linearity ⁵	I_{NL}		+/- 3	+/- 5	LSB ⁶
Differential non-Linearity ⁵	DNL		+/- 0.6	+/- 1	LSB ⁶
Monotonicity					
Offset ⁷ <ul style="list-style-type: none"> ≤15 MHz ADC Clock Internal/External Reference >15 MHz ADC Clock Internal/External Reference 	V_{OFFSET}	+/- 4.03 +/- 7.25	+/- 8.86 +/- 13.70		mV
Gain Error	E_{GAIN}		0.801 to 0.809	0.798 to 0.814	mV
AC Specifications⁸					
Signal to Noise Ratio	SNR		59		dB
Total Harmonic Distortion	THD		64		dB
Spurious Free Dynamic Range	SFDR		65		dB
Signal to Noise plus Distortion	SINAD		59		dB
Effective Number of Bits	ENOB		9.5		bits
ADC Inputs					
Input Leakage Current	I_{IN}		0	+/-2	μA
Input Injection Current ⁹	I_{INJ}			+/-3	mA
Input Capacitance Sampling Capacitor <ul style="list-style-type: none"> 1x mode 2x mode 4x mode 	C_{ADI}		1.4 2.8 5.6		pF

1. If the ADC's reference is from V_{DDA} : When V_{DDA} is below 3.0 V, the ADC functions but ADC specifications are not guaranteed.
2. When the input is at the V_{refl} level, the resulting output will be all zeros (hex 000), plus any error contribution due to offset and gain error. When the input is at the V_{refh} level the output will be all ones (hex FFF), minus any error contribution due to offset and gain error.
3. ADC clock duty cycle min/max is 45/55%
4. When V_{refh} is supplied externally
5. I_{NL} measured from $V_{IN} = V_{REFL}$ to $V_{IN} = V_{REFH}$
6. LSB = Least Significant Bit = 0.806 mV at 3.3 V V_{DDA} , x1 Gain Setting

Table 29. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
V_H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	13	mV
	• CR0[HYSTCTR] = 01	—	10	48	mV
	• CR0[HYSTCTR] = 10	—	20	105	mV
	• CR0[HYSTCTR] = 11	—	30	148	mV
V_{CMPOh}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1) ²		50		ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)		250		ns
	Analog comparator initialization delay ³	—	—	40	μ s
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μ A
	6-bit DAC reference inputs, Vin1 and Vin2 There are two reference input options selectable (via VRSEL control bit). The reference options must fall within this range.	V_{DDA}	—	V_{DD}	V
INL	6-bit DAC integral non-linearity	−0.5	—	0.5	LSB ⁴
DNL	6-bit DAC differential non-linearity	−0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to $V_{DD}-0.6V$.

2. Signal swing is 100 mV

3. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

4. 1 LSB = $V_{reference}/64$

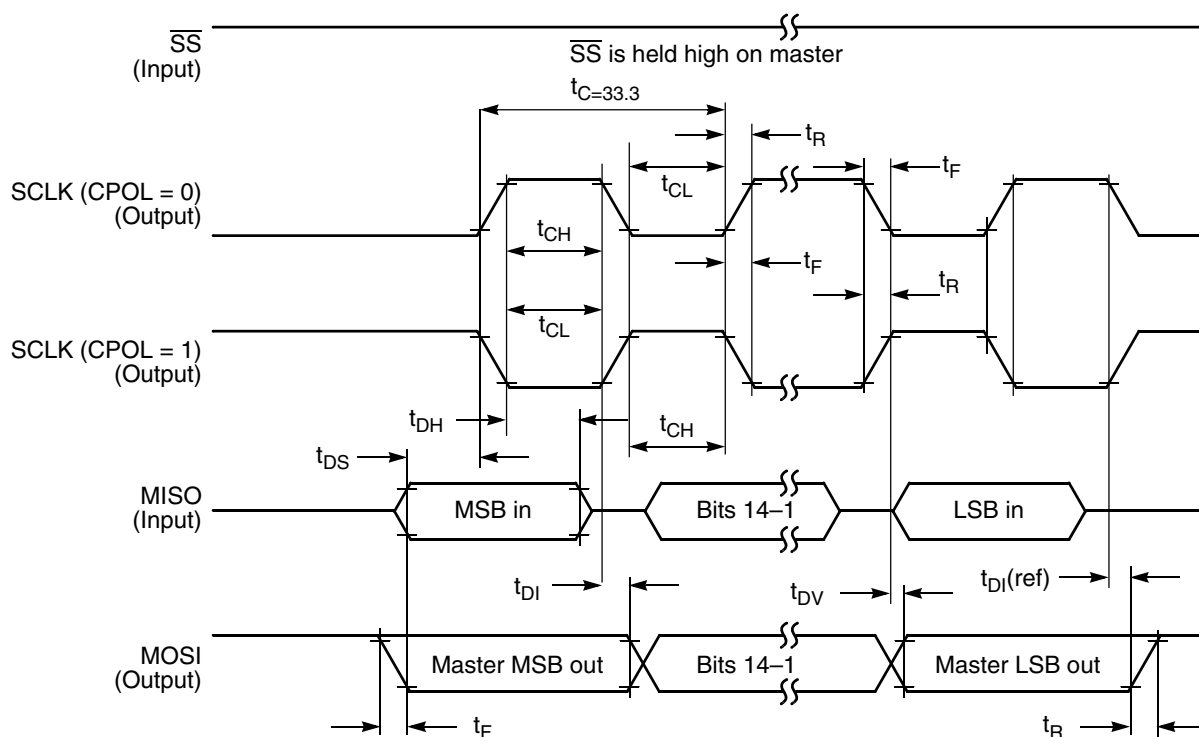


Figure 15. SPI Master Timing (CPHA = 0)

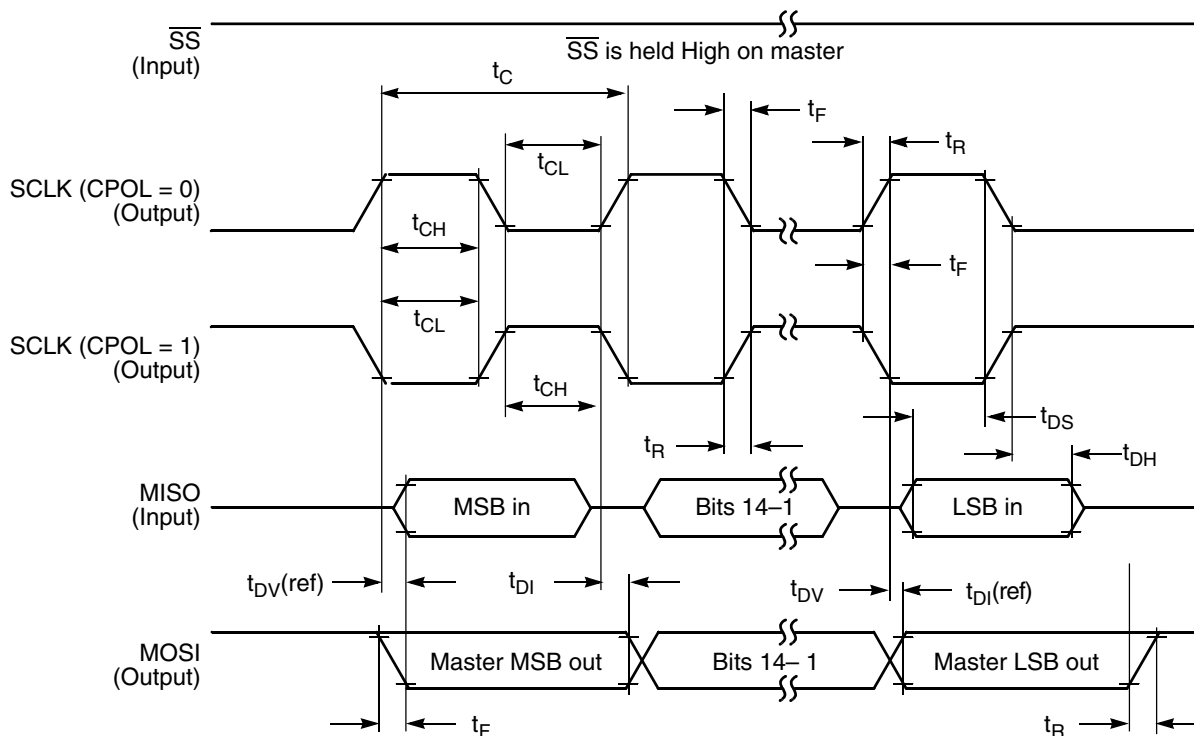


Figure 16. SPI Master Timing (CPHA = 1)

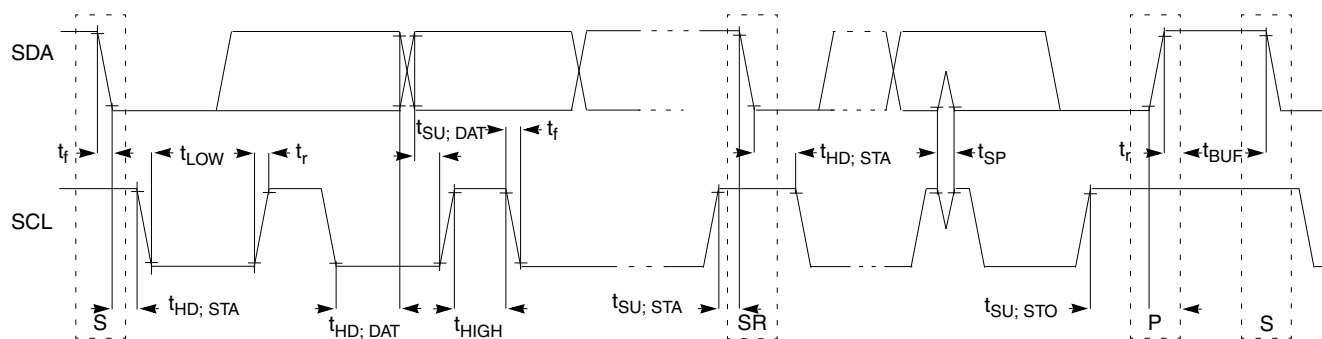


Figure 22. Timing Definition for Fast and Standard Mode Devices on the I²C Bus

9 Design Considerations

9.1 Thermal Design Considerations

An estimation of the chip junction temperature, T_J , can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

Where,

T_A = Ambient temperature for the package (°C)

$R_{\theta JA}$ = Junction-to-ambient thermal resistance (°C/W)

P_D = Power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single-layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low-power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

Where,

$R_{\theta JA}$ = Package junction-to-ambient thermal resistance (°C/W)

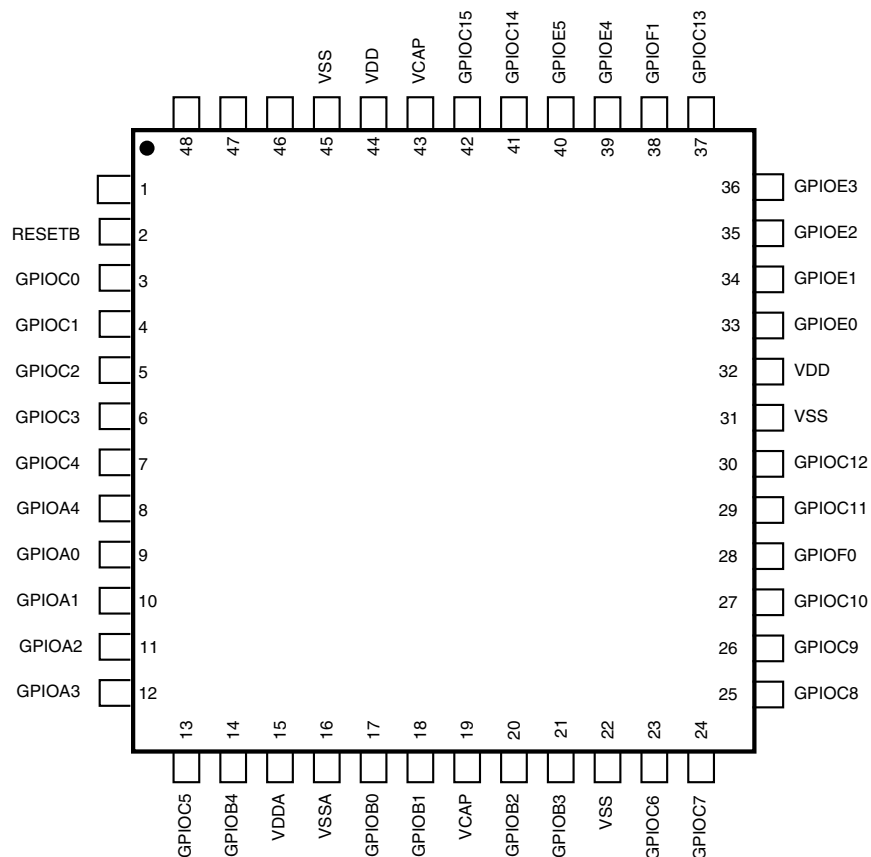


Figure 24. 48-pin LQFP

12 Product Documentation

The documents listed in [Table 36](#) are required for a complete description and proper design with the device. Documentation is available from local Freescale distributors, Freescale Semiconductor sales offices, or online at <http://www.freescale.com>.

Table 36. Device Documentation

Topic	Description	Document Number
DSP56800E/DSP56800EX Reference Manual	Detailed description of the 56800EX family architecture, 32-bit digital signal controller core processor, and the instruction set	DSP56800ERM
MC56F844xx Reference Manual	Detailed functional description and programming model	MC56F844XXRM
Serial Bootloader User Guide	Detailed description of the Serial Bootloader in the DSC family of devices	TBD
MC56F844xx Data Sheet	Electrical and timing specifications, pin descriptions, and package information (this document)	MC56F844XX
MC56F84xxx Errata	Details any chip issues that might be present	MC56F84XXX_0N27E

13 Revision History

The following table summarizes changes to this document since the release of the previous version.

Table 37. Revision History

Rev.	Date	Substantial Changes
2	06/2012	This is the first publicly released version of this document.